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Application Serial No. 10/615,899 Reply to office action of March 21, 2007 PATENT Docket: CU-3282

## Amendments to the Claims

The listing of claims presented below will replace all prior versions, and listings, of claims in the application.

## Listing of claims:

What is claimed is:

1. (Currently amended) A method for improving reliability of an etching apparatus and a deposition apparatus, which etching and deposition apparatus' use chlorine-containing etching and deposition gases respectively, the method comprising the steps of:

generating a <u>first</u> plasma in the apparatus that consists essentially of hydrogen and 5% to 90% argon;

and, after the first plasma is generated, generating a second plasma in the apparatus, the second plasma consisting essentially of nitrogen and 5% to 90% argon in the reaction unit to remove a chlorine-containing residual gas remaining in a reaction tube of the reaction unit.

- 2. (Cancelled)
- 3. (Cancelled)
- 4. (Cancelled)
- 5. (Cancelled)
- 6. (Cancelled)
- 7. (Cancelled)

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- 8. (Cancelled)
- 9. (Cancelled)
- 10. (Cancelled)
- 11. (Currently amended) A method for improving reliability of an etching apparatus and a deposition apparatus, which etching and deposition apparatus' use chlorine-containing etching and deposition gases respectively, the method comprising the steps of:

generating a <u>first plasma</u> in the apparatus that consists essentially of nitrogen and 5% to 90% hydrogen in the reaction unit to remove a chlorine-containing residual gas that remains in a reaction tube of the reaction unit and

after the first plasma is generated, generating a second plasma in the apparatus that consists essentially of hydrogen in the reaction unit.

12. (Currently amended) A method for improving reliability of an etching apparatus and a deposition apparatus, which etching and deposition apparatus' use chlorine-containing etching and deposition gases respectively, the method comprising the steps of:

generating a <u>first plasma</u> in the apparatus that includes hydrogen and <u>5%</u> to <u>90% argon</u> nitrogen in the reaction unit to remove a chlorine-containing residual gas remaining in a reaction tube of the reaction unit, <del>wherein the plasma consists essentially of nitrogen, hydrogen of 5 to 50% and argon of 5 to <u>90%</u>.; and,</del>

generating a second plasma in the apparatus that includes nitrogen and a

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combination of 5% to 90% hydrogen and 5% to 90% argon.